

N-channel TrenchMOS standard level FET Rev. 02 — 16 March 2010

**Product data sheet** 

#### **Product profile** 1.

#### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

### **1.3 Applications**

- 12 V and 24 V loads
- Automotive and general purpose power switching

#### 1.4 Quick reference data

#### Table 1. Quick reference

Suitable for standard level gate drive
sources

Suitable for thermally demanding environments due to 175 °C rating

nexperia

Motors, lamps and solenoids

	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	55	V
I <sub>D</sub>	drain current	$V_{GS} = 5 \text{ V}; T_{mb} = 25 \text{ °C};$ see <u>Figure 1</u> and <u>3</u>	-	-	38	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	88	W
Avalanc	he ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 34 A; V <sub>sup</sub> ≤ 55 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped	-	-	58	mJ
Dynamic	characteristics					
$Q_{GD}$	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 44 \text{ V}; \text{ see } \frac{\text{Figure } 14}{100000000000000000000000000000000000$	-	9	-	nC
Static ch	aracteristics					
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; see <u>Figure 11</u> and <u>12</u>	-	26	30	mΩ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S
			SOT428 (DPAK)	

## 3. Ordering information

#### Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7230-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

### 4. Limiting values

#### Table 4.Limiting values

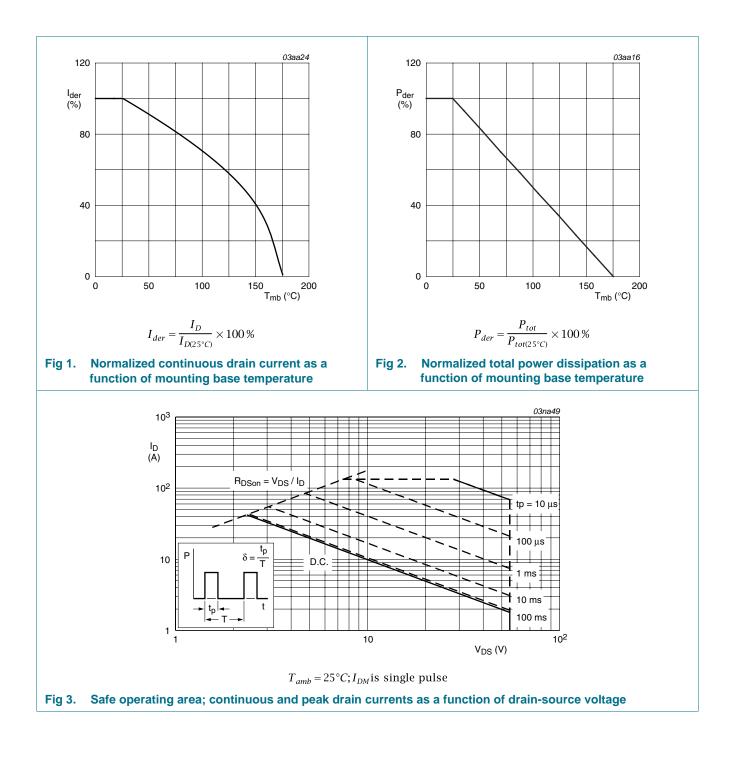
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
V <sub>DGR</sub>	drain-gate voltage	R <sub>GS</sub> = 20 kΩ		-	55	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$T_{mb}$ = 25 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u> and <u>3</u>		-	38	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 5 V; see <u>Figure 1</u>		-	27	А
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 3</u>	<u>[1]</u>	-	150	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	88	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	ain diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	38	А
I <sub>SM</sub>	peak source current	$t_p \le 10 \ \mu s$ ; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	150	А
Avalanche	ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_D = 34 \text{ A};  \text{V}_{sup} \leq 55 \text{ V};  \text{R}_{GS} = 50  \Omega;  \text{V}_{GS} = 10 \text{ V}; \\ T_{j(\text{init})} = 25 ^\circ\text{C}; \text{ unclamped} \end{array}$		-	58	mJ

[1] Peak drain current is limited by chip, not package.

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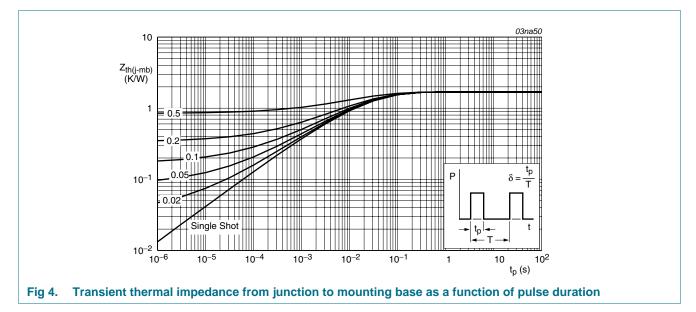
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### 5. Thermal characteristics

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Table 5.	Inermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting ba	se	-	-	1.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	see Figure 4	-	71.4	-	K/W



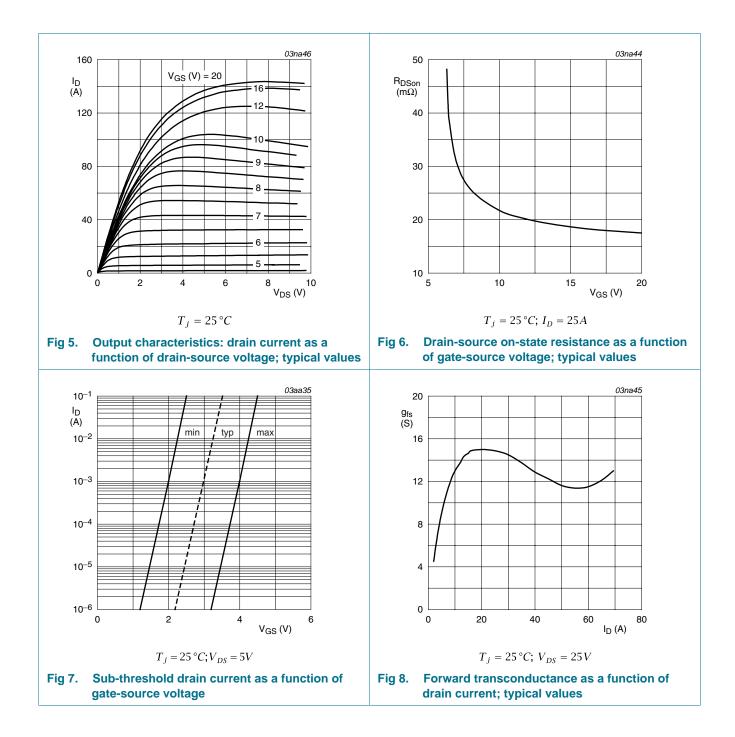
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### 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
V <sub>GS(th)</sub>	gate-source threshold	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{10}$	2	3	4	V
	voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; \text{ see } \frac{\text{Figure } 10}{10}$	-	-	4.4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}; \text{ see } Figure 10$	1	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = 55 V; $V_{GS}$ = 0 V; $T_j$ = 175 °C	-	-	500	μA
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μA
I <sub>GSS</sub>	gate leakage current	$V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{DS} = 0 \text{ V}; V_{GS} = -10 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 175 °C; see Figure 11 and 12	-	-	60	mΩ
		$V_{GS}$ = 10 V; $I_{D}$ = 25 A; $T_{j}$ = 25 °C; see Figure 11 and 12	-	26	30	mΩ
Dynamic	characteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 14}{100000000000000000000000000000000000$	-	24	-	nC
Q <sub>GS</sub>	gate-source charge		-	5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	9	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ °C};$ see Figure 15	-	864	1152	pF
C <sub>oss</sub>	output capacitance		-	218	262	pF
C <sub>rss</sub>	reverse transfer capacitance			139	191	pF
d(on)	turn-on delay time	$V_{DS}$ = 30 V; R <sub>L</sub> = 1.2 Ω; $V_{GS}$ = 5 V;	-	14	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	68	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	83	-	ns
t <sub>f</sub>	fall time		-	43	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain lead from package to centre of die; $T_j = 25 \text{ °C}$	-	2.5	-	nH
L <sub>S</sub>	internal source inductance	measured from drain lead from package to source bond pad	-	7.5	-	nH
Source-d	rain diode					
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; see <u>Figure 13</u>	-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = -10 V;	-	40	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 30 \text{ V}; \text{ T}_{i} = 25 \text{ °C}$	-	100	-	nC

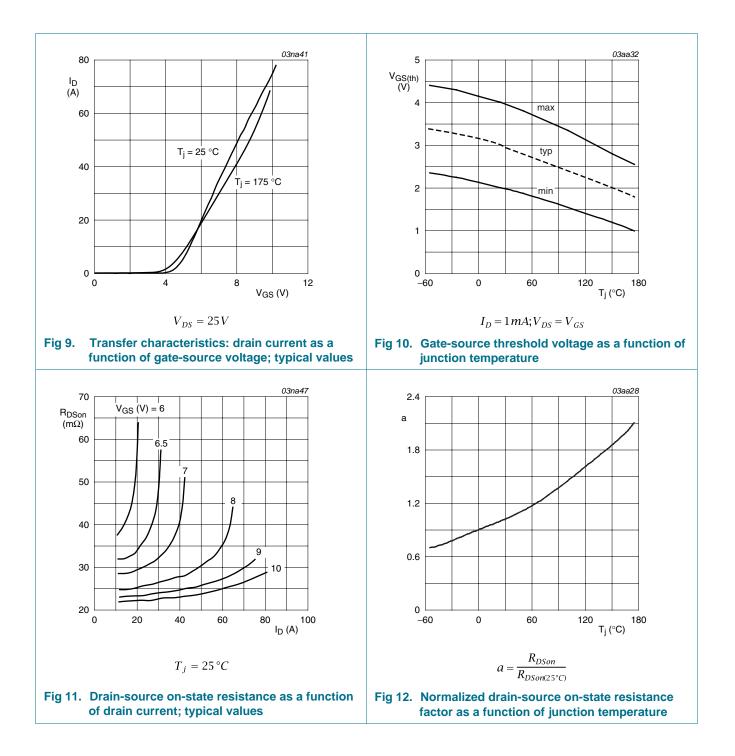
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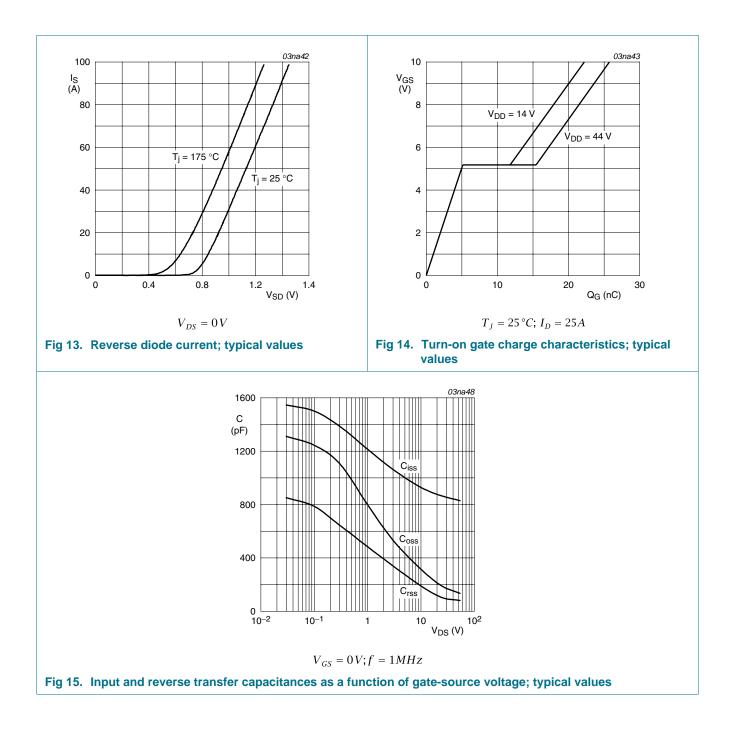
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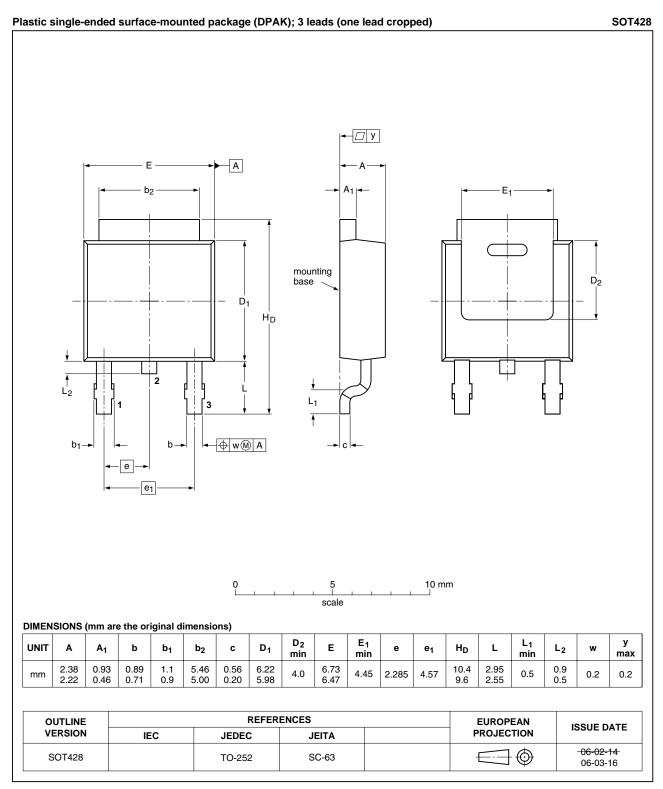
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### 7. Package outline



#### Fig 16. Package outline SOT428 (DPAK)

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BUK7230-55A\_2

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## 8. Revision history

n history			
Release date	Data sheet status	Change notice	Supersedes
20100316	Product data sheet	-	BUK7230_55A-01
		•	ly with the new identity
<ul> <li>Legal texts</li> </ul>	have been adapted to the	ne new company name v	where appropriate.
20000929	Product specification	-	-
-	20100316 • The format guidelines of • Legal texts	Release date       Data sheet status         20100316       Product data sheet         • The format of this data sheet has be guidelines of NXP Semiconductors.         • Legal texts have been adapted to the semiconduct of the se	Release date         Data sheet status         Change notice           20100316         Product data sheet         -           • The format of this data sheet has been redesigned to comp guidelines of NXP Semiconductors.         -           • Legal texts have been adapted to the new company name of         -

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Document status [1][2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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